

This listing of claims will replace all prior versions and listings of claims in the application:

Listing of Claims:

Claims 1-51. (Canceled)

52. (Currently Amended) A single crystal silicon wafer having a central axis, a front side and a back side which are generally perpendicular to the axis, a circumferential edge, and a radius extending from the central axis to the circumferential edge of the wafer, the wafer comprising:

5 an interstitial-dominated, axially symmetric region extending radially inward from the circumferential edge which is substantially free of A type agglomerated interstitial defects; and,

10 a vacancy-dominated, axially symmetric region extending radially inward from the interstitial-dominated region and containing agglomerated vacancy defects, wherein the concentration of agglomerated vacancy defects is greater than 10^3 defects/cm³, and further wherein, upon being subjected to an oxidation treatment, an oxidation induced stacking fault concentration is less than about 50/cm².

53. (Original) The wafer of claim 52 wherein the interstitial-dominated, axially symmetric region is also substantially free of B type agglomerated defects.

54. (Currently Amended) The wafer of claim 52 wherein the wafer has a radius diameter of at least ~~about~~ 150 mm.

55. (Original) The wafer of claim 52 wherein the interstitial-dominated, axially symmetric region has a radial width of about 40% of the length of the radius of the ingot.

56. (Previously Presented) The wafer of claim 52 wherein the interstitial-dominated, axially symmetric region has a radial width of about 60% of the length of the radius of the ingot.

57: (Original) The wafer of claim 52 wherein the average oxygen content of the wafer is within the range of about 11 to about 14.5 PPMA.

58. (Original) The wafer of claim 52 wherein the average oxygen content of the wafer is within the range of about 14.5 to about 18 PPMA.

59. (Original) The wafer of claim 52 wherein the oxidation induced stacking fault concentration of the wafer is less than about 40/cm².

60. (Original) The wafer of claim 52 wherein the oxidation induced stacking fault concentration of the wafer is less than about 20/cm².

61. (Original) The wafer of claim 52 wherein the oxidation induced stacking fault concentration of the wafer is less than about 10/cm².

62. (Original) The wafer of claim 52 wherein the number of light point defects equal to or greater than about 0.12 microns in size on the wafer surface is less than about 25.

63. (Original) The wafer of claim 52 wherein the number of light point defects equal to or greater than about 0.12 microns in size on the wafer surface is less than about 10.

Claims 64-72. (Canceled)

73. (New) The wafer of claim 52 wherein the interstitial-dominated, axially symmetric region has a radial width of about 20% of the length of the radius of the ingot.

74. (New) The wafer of claim 52 wherein the interstitial-dominated, axially symmetric region has a radial width of about 80% of the length of the radius of the ingot.

75. (New) The wafer of claim 52 wherein the wafer has a diameter of at least 200 mm.

76. (New) The wafer of claim 75 wherein the interstitial-dominated, axially symmetric region is also substantially free of B type agglomerated defects.

77. (New) The wafer of claim 75 wherein the interstitial-dominated, axially symmetric region has a radial width of about 40% of the length of the radius of the ingot.

78. (New) The wafer of claim 75 wherein the interstitial-dominated, axially symmetric region has a radial width of about 60% of the length of the radius of the ingot.

79. (New) The wafer of claim 75 wherein the average oxygen content of the wafer is within the range of about 11 to about 14.5 PPMA.

80. (New) The wafer of claim 75 wherein the average oxygen content of the wafer is within the range of about 14.5 to about 18 PPMA.

81. (New) The wafer of claim 75 wherein the oxidation induced stacking fault concentration of the wafer is less than about $20/\text{cm}^2$.

82. (New) The wafer of claim 75 wherein the number of light point defects equal to or greater than about 0.12 microns in size on the wafer surface is less than about 25.

83. (New) The wafer of claim 52 wherein the wafer has a diameter of at least 300 mm.

84. (New) The wafer of claim 83 wherein the interstitial-dominated, axially symmetric region is also substantially free of B type agglomerated defects.

85. (New) The wafer of claim 83 wherein the interstitial-dominated, axially symmetric region has a radial width of about 40% of the length of the radius of the ingot.

86. (New) The wafer of claim 83 wherein the interstitial-dominated, axially symmetric region has a radial width of about 60% of the length of the radius of the ingot.

87. (New) The wafer of claim 83 wherein the average oxygen content of the wafer is within the range of about 11 to about 14.5 PPMA.

88. (New) The wafer of claim 83 wherein the average oxygen content of the wafer is within the range of about 14.5 to about 18 PPMA.

89. (New) The wafer of claim 83 wherein the oxidation induced stacking fault concentration of the wafer is less than about 20/cm².

90. (New) The wafer of claim 83 wherein the number of light point defects equal to or greater than about 0.12 microns in size on the wafer surface is less than about 25.